

ABSTRACT

A technique is provided in which an offset magnetic field of a memory cell of a MRAM is reduced more effectively. The MRAM of the present invention is composed of a free layer (11) which has a reversible free spontaneous magnetization, a fixed layer (6) which has fixed spontaneous magnetization, and a spacer layer (10) formed of non-magnetic interposed between the free layer (11) and the fixed layer (6). The fixed layer (6) is formed such that orange peel effect and magneto-static coupling effect does not substantially influence on the free layer (11).